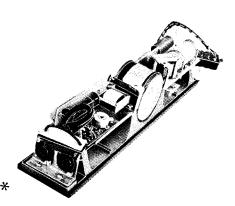


MASTR Progress Line

12-VOLT, 70/90/100-WATT POWER SUPPLY MODEL 4EP37A10



SPECIFICATIONS*

Type Number	EP-37-A	
Output	Voltage	Current
Regulated Receiver	10 volts	150 mA
Regulated Transmitter 25 — 88 MHz 132 — 470 MHz	-20 volts -20 volts	45 mA 90 mA
Bias	-45 volts	
Low B-Plus 25 — 88 MHz 132 — 174 MHz 406 — 470 MHz	300 volts 300 volts 300 volts	70 mA 110 mA 95 mA
High B-Plus 25 — 88 MHz 132 — 174 MHz 406 — 470 MHz	660 volts 680 volts 660 volts	280 mA 220 mA 270 mA
Battery Drain		
Transmit 25 — 88 MHz 132 — 174 MHz 406 — 470 MHz	13.4 volts 13.4 volts 13.4 volts	25 amps 26 amps 26 amps
Receive Standby - Squelched Standby - Unsquelched Squelched - Transmitter Filaments On		150 mA 1.1 amps amps (250 — 88 MHz)
		amps (132 — 174 MHz) amps (406 — 470 MHz)
Transistors Multivibrator Circuit 10-Volt Regulator Circuit -20 Volt Regulator Circuit	4 3 2	
Rectifiers	10	
Zener Diodes	2	
Battery Voltage	13.4 volts ±20% (positive or nega 12-volt system)	tive ground,
Duty Cycle	Transmit: 20% (one minute transm	nit, four minutes off)
Ambient Temperature Range	-30°C (-22 $^{\circ}\text{F}$) to $+60^{\circ}\text{C}$ (+140 $^{\circ}\text{F}$)	

*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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WARNING -

No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

DESCRIPTION

Transistorized Power Supply Model 4EP37Al0 is used with 12-volt, 70-Watt, 90-watt and 100-watt MASTR mobile combinations. The power supply provides:

- Plate, screen and bias voltages for the tubed transmitter multiplier and poweramplifier stages.
- Regulated -20 volts for the transistorized transmitter exciter board.
- Regulated +10 volts for the receiver and for the transmitter Channel Guard board.

Low voltage for the transmitter filaments and receiver audio amplifier is taken directly from the vehicle battery.

The fully transistorized power supply uses highly efficient silicon rectifiers for reliable operation. The use of Mylar® capacitors provides additional reliability, with good performance at low temperatures. Regulation of critical transmitter and receiver supply voltages provides improved operation over the wide range of input voltages encountered in mobile communications.

CIRCUIT ANALYSIS

The power supply may be used in vehicles having either positive or negative ground systems. The power cable, fused leads and ground wire must be connected for the proper polarity when the Two-Way Radio is installed.

All connections to the transmitter, receiver and power cables are made through two plug connectors. Two clip-on connectors (P501 and P502) connect the power supply to the push-to-talk relay on the system frame. Figure 2 is a simplified power distribution and switching diagram.

MULTIVIBRATOR CIRCUIT (Figure 1)

Power Supply Model 4EP37A10 uses transistors as switches in two identical inductively coupled multivibrator circuits. These switches connect the battery voltage across alternate halves of the transformer primary-resulting in alternating square waves. The output of each multivibrator circuit (square wave generator) is stepped up by the power transformer; then rectified and filtered to supply B-plus and bias voltages for the transmitter.

The two identical multivibrator circuits operate in parallel pairs (Q501-Q503 and Q502-Q504). Separate bias parallel windings are used to provide equal load sharing between the paired transistors. Since both multivibrators operate in the same manner, a description of the operation of Q501 and Q502 only will be given.

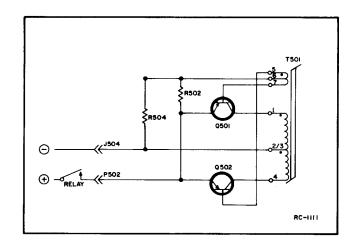


Figure 1 - Simplified Multivibrator Circuit

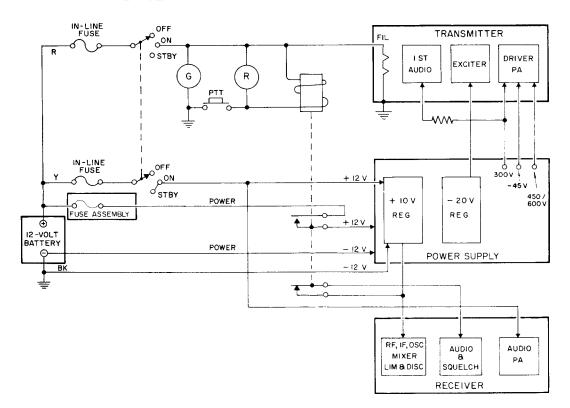
Keying the transmitter closes the relay contacts and applies power to transistors Q501 and Q502. The bases of the transistors are biased negatively (with respect to their emitters) through resistor R504, and all transistors start to conduct. Due to inherently different characteristics, one transistor will conduct slightly more than the others.

Assuming that Q501 will initially conduct more than Q502, Q501 will draw more current through winding 1-2/3 than Q502 will draw through winding 2/3-4, making terminal 1 of T501 more positive than terminal 4.

The increasing magnetic field in the core of T501 induces a voltage in the windings 5-6-7, causing terminal 7 to become negative with respect to the emitter of Q501. This increased bias causes Q501 to conduct even harder. At the same time, terminal 5 becomes positive with respect to the emitter Q502, stopping current flow through Q502 and winding 2/3-4. Current through winding 1-2/3 rapidly saturates the core of the transformer, and the magnetic field ceases to increase.

The voltage induced in winding 5-6-7 therefore falls to zero, reducing the bias on Q501 to that obtained through R504. This reduced bias tends to cut off Q501 and

12 VOLT NEGATIVE GROUND



RC-1168A

12 VOLT POSITIVE GROUND

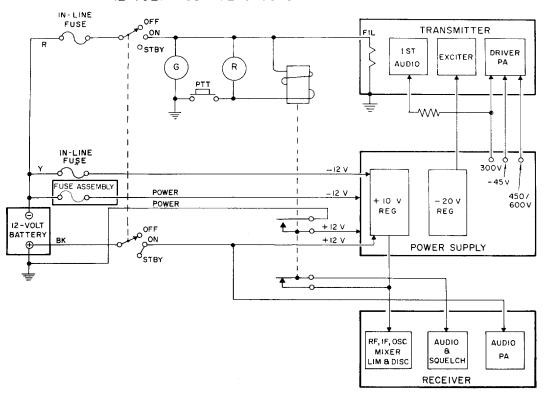


Figure 2 - 12-Volt Power Distribution Diagram

RC-1169A

reduce the current through winding 1-2/3.

The collapsing magnetic field in T501 induces a reverse biasing voltage across winding 5-6-7, biasing Q501 off and biasing Q502 on. Q502 now conducts in a similar manner until T501 is again saturated. Resistor R502 limits the base current which can flow through Q501 and Q502.

The two transistor pairs continue to conduct alternately at a frequency of approximately 1330 hertz. The resulting waveform approaches that of a perfect square wave.

RECTIFIER AND FILTER CIRCUITS

Negative Bias and -20 Volt Regulator (Figure 3) - The AC voltage developed across secondary windings 12-8-14 of transformer T501 is rectified by full-wave rectifiers CR501 and CR502, and is filtered by C501, L502 and C502. The negative 45 volts is the bias voltage for the control grids of the transmitter driver and power amplifier. This circuit also supplies -45 volts to input of the 20-Volt Regulator. The bias voltage is present as a protective measure to limit cathode current in the PA tube while the PA is untuned, or in case of loss of drive to the PA.

Transmitter Multiplier B-Plus (Figure 4) - The AC voltage developed across high voltage secondary windings 18-21 of T501 is rectified by using a bridge rectifier circuit consisting of CR503, CR504, CR505 and CR506. Filtering is provided by filter C505, L501 and C506. Relatively small values of L and C are required because of the high frequency and the square wave characteristics of the AC voltage.

Power Amplifier B-Plus (Figure 4) - The AC voltage developed across the high voltage secondary windings 15-17 of T501 is rectified by the bridge rectifier circuit, CR507.

CR508, CR509 and CR510. The output of this bridge rectifier circuit is connected in series with the multiplier B-plus bridge circuit to provide the high B-plus output. Filtering is provided by C507. R510 and R511 are bleeder resistors for discharging C507 when the keying relay is opened. R505 prevents ringing in the oscillator circuit formed by C505, L501 and C506.

-20 VOLT REGULATOR (Figure 5)

The -20 Volt Regulator provides a closely controlled supply voltage for the transistorized exciter section of the transmitter. Input power is taken from the -45 volt bias output at TB1-3. Dropping resistor R507 provides the negative bias to turn on Q506. Zener diode VR501 provides a voltage reference for the regulator.

When the input voltage at TB1-3 rises, the output voltage at the emitter of Q506 also tends to rise. This causes a change in the base-emitter bias on Q507, making it conduct more heavily. When Q507 conducts, there is less base bias on Q506, and less base current. With less current, the voltage drop across Q506 is larger; and the output voltage remains constant.

When the input voltage starts to drop, the output voltage also tends to drop; and Q507 will conduct less. This increases the forward bias on Q506 and reduces the voltage drop across the transistor so that the output voltage remains constant.

Capacitor C511 prevents high frequency oscillation.

R506, R508 and R512 form an adjustable voltage divider so that potentiometer R508 can be adjusted for a -20 volt output. R509 provides bias current for VR501. The output is metered at the transmitter centralized metering jack J102-12.

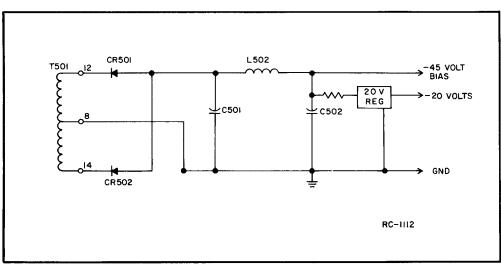


Figure 3 - Simplified Bias and -20 Volt Regulator Supply Circuit

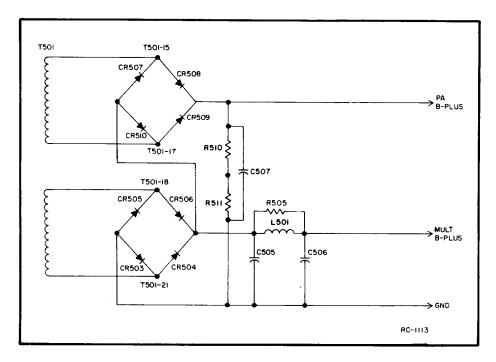


Figure 4 - Simplified Transmitter Multiplier and Power Amplifier B-Plus Circuits

10-VOLT REGULATOR A501

The 10-Volt Regulator Circuit provides a closely controlled supply voltage for the receiver (except for the audio amplifier), and a supply voltage for the transmitter Channel Guard option, when present. Input voltage is supplied from the Control Unit on P505-5.

When the supply voltage (or output) starts to increase, the voltage at the base

of Q1 also increases. As the emitter voltage of Q1 is kept constant by VR1, the emitter-base voltage increases. This causes Q1 to conduct more which means less base current for Q505. The voltage drop across Q505 becomes larger and the output remains constant.

When the input voltage starts to drop, the output voltage also tends to drop and Q1 will conduct less. This increases the forward bias on Q505 and reduces the voltage

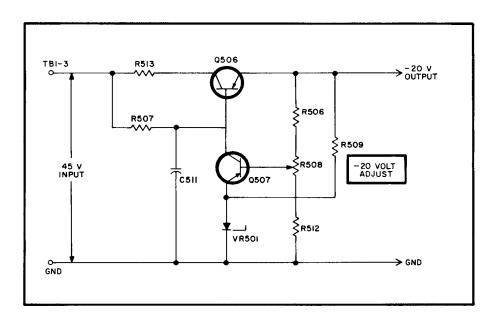


Figure 5 - -20 Volt Regulator Circuit

drop across Q505 to keep the output constant.

Diode CR1 gives reverse polarity protection to the supply. Potentiometer R4 is used to set the emitter-base voltage of Q1 for the desired 10-Volt ±5% output. R1 and R3 limit maximum current through Q1. R2 provides bias current for Zener diode VR1, and R7 provides bias for Q505, C1 and C3 prevent high frequency oscillation. The output voltage is metered at P505-7.

RECEIVER MUTING

Transistor Q2 on the 10-volt regulator board operates as a switch for the receiver muting +10 volts. When the transmitter is not keyed, the base of Q2 is connected to ground, causing Q2 to conduct. When conducting, the +10 volts at the collector of Q2 is coupled from P505 to the base of receiver DC amplifier Q9, turning it on. With Q9 conducting, Q10 is turned off, allowing the receiver to operate normally.

Keying the transmitter applies +12 volts to the base of the PNP muting switch (Q2), turning it off. This removes the +10 volts to receiver DC amplifier Q9, turning it off. Turning off Q9 causes DC amplifier Q10 to turn on, which turns off the receiver audio stages and mutes the receiver.

MAINTENANCE

HEAT SINK SERVICING

Since the metal envelopes of the transistors are at collector potential, they must be electrically isolated from ground. However, there must be a good path for heat from the transistors to reach the cast aluminum radiator (heat sink) in which they are mounted, so that the heat will be dissipated by the heat sink. The anodized aluminum spacers used between the transistors and their mounting plate not only isolate the transistors electrically, but also provide a good conductor to conduct heat away from them.

Silicone grease is used between the metal parts in the heat sink to improve contact between them and allow the heat to be transferred more readily.

NOTE —

Whenever the transistor mounting plate is removed from the heat sink, be sure that there is sufficient silicone grease on the plate to make good contact with the heat sink before it is replaced. There should also be a coating of grease beneath the transistors and beneath the anodized aluminum spacers.

REINSTALLATION

If the mobile combination is ever moved to a different vehicle, be sure to check the battery polarity of the new system and, if necessary, change the power cable connections to the fuse assembly, as well as the ignition switch cable connections, to maintain current polarity.

DISASSEMBLY

To service the power supply --

- Pull the locking handle down and pull radio out of mounting frame.
- Remove the two screws in bottom cover and take off cover.

To remove the power supply from the system frame --

- 1. Complete Steps 1 and 2 above.
- 2. Remove the two Phillips-head retaining screws in the front casting, and pull casting away from system frame.
- 3. Pry power connector out of connector supporting bracket. Next, unplug the clip-on connectors to the system relay, and unplug systems connector at the back of the power supply.
- Lift the Two-Way Radio away from power supply.

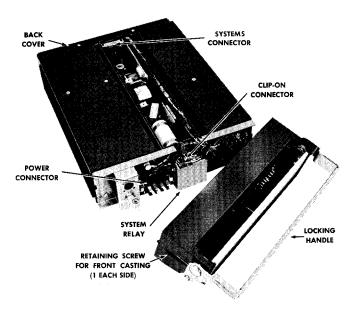
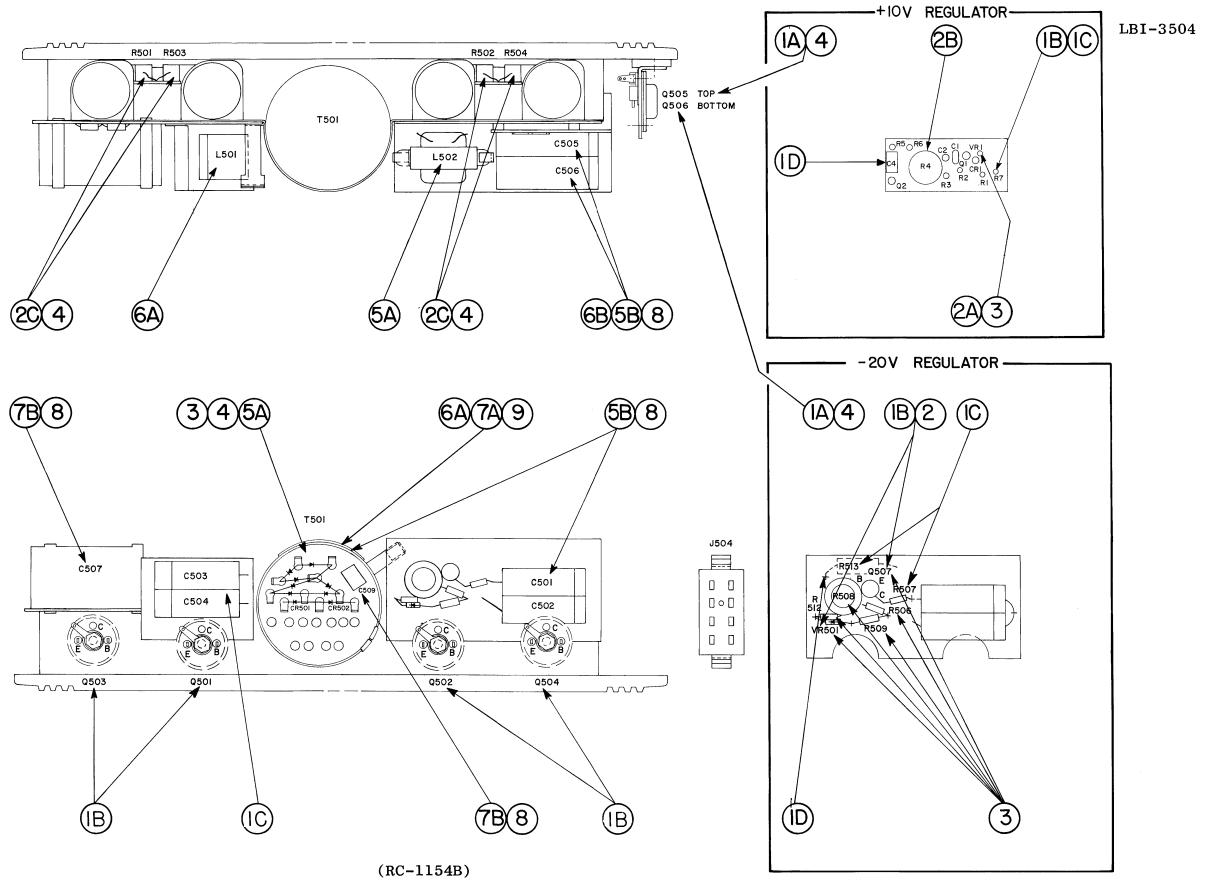


Figure 6 - Disassembly of Power Supply

STEP 1 - QUICK CHECKS

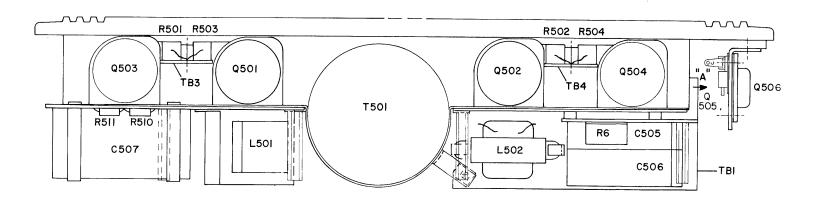
SYMPTOM	PROCEDURE
No power supply output voltages at P505 when unit is keyed	Check for 12 Volts at J504-3-7. If O.K., go to Step 2; otherwise check:
	1. A. Check fuse assembly for open circuit. If fuse is open check for:
	B. Collector-to-emitter short in Q501, Q502, Q503, Q504, primary wiring shorts.
	C. If an above transistor is shorted, check for shorted C504, C503.
	With 12 Volts at J504, check the following steps:
	2. A. Open fuse in system cable.
	B. Keying relay in system should close when PTT switch is depressed.
	C. Open R501, R502, R503, R504.
	3. Check T501 for shorts and opens. Check for shorted winding turns by applying a 1/2-volt P-P from an audio signal generator to the primary winding T501. Check output of each secondary winding with a scope. No output indicates shorted turns.
Output voltages low	4. Open R501, R502, R503, R504, and diodes in affected circuit.
No -45 Volts at P505-2	5. A. Open CR501, CR502, L502, T501.
	B. Shorted C502, C501, T501.
No 300 Volts at P505-1	6. A. Open CR503, CR504, CR505, CR506, L501, T501.
	B. Shorted C505, C506.
No 650 Volts at P505-9	7. A. Open CR507 through CR510 (two or more), T501.
	B. Shorted C507, C509.
Excessive output ripple voltages	8. Open diodes, C501, C502, C505, C506, C507, C509.
Reverse or high output voltage on bias output	9. Check for shorts between bias output winding and B+ output winding of T501.
	10 VOLT REGULATOR
No 10-Volts regulated at P505-7	1. Check for the following:
	A. Open Q505.
	B. 12 Volts input.
	C. Open R7.
	D. Shorted C4.
	E. Open fuse in vehicle system.
Output voltage too high, cannot be adjusted by R6	2. A. Check for open VR1.
	B. Defective R4.
Very low output voltage	3. Check for a shorted VR1.
Output voltage equals input voltage	4. Shorted Q505.
N- 00 W 14	-20 VOLT REGULATOR
No -20 Volts regulated at P505-3	1. Check for the following:
	A. Open Q506.
	B. Shorted Q507 and/or VR501.
	C. Open R507, R513.
	D45 Volts at TB1-18.
Very low output voltage	2. Shorted Q507 or VR501.
Output voltage too high, cannot be adjusted by R508	3. Open VR501, Q507, R506, R508, R509, R512.
Output voltage equals input voltage	4. Shorted Q506.

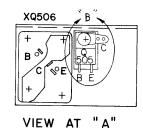


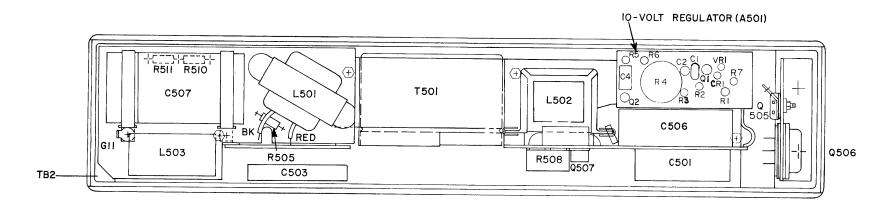
TROUBLESHOOTING PROCEDURE

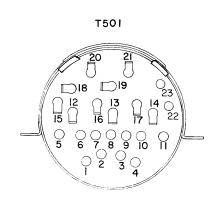
70/90/100-WATT POWER SUPPLY MODEL 4EP37A10

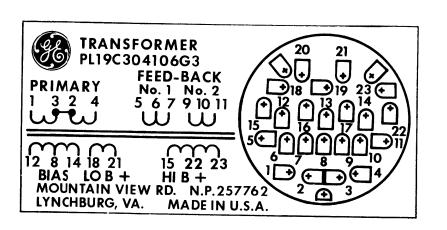


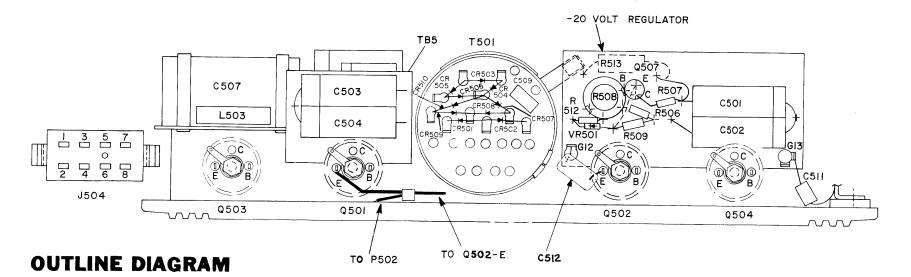












70/90/100-WATT POWER SUPPLY

RESISTANCE READINGS

- LEAD

TO GRD

+ LEAD

TO GRD

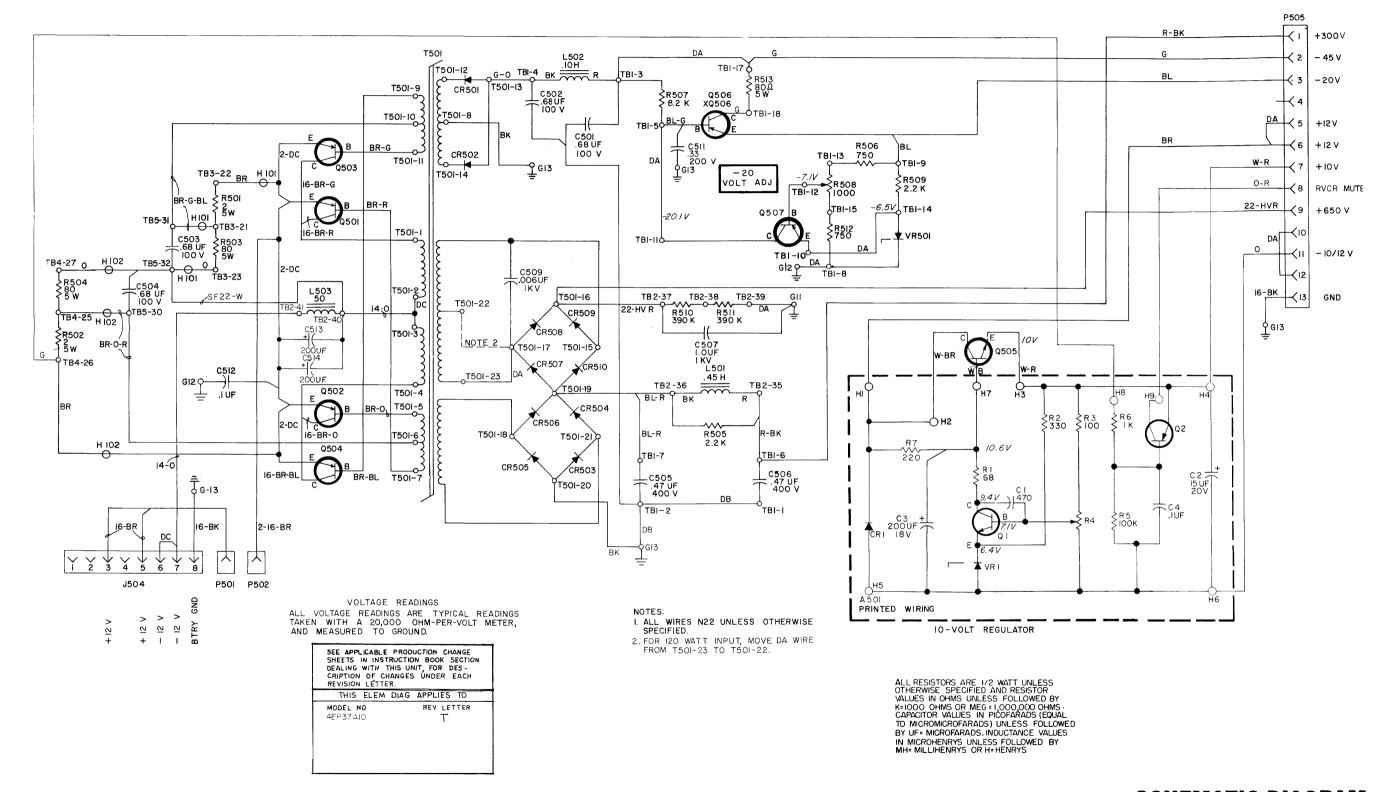
ALL RESISTANCE READINGS ARE TYPICAL READINGS
TAKEN WITH A 20,000 OHMS-PER-VOLT METER TO CHASSIS GROUND.

- LEAD

TO GRD

TO GRD

19D402567, Rev. 10)



(19D402304, Rev. 24)

SCHEMATIC DIAGRAM

70/90/100-WATT POWER SUPPLY MODEL 4EP37A10

LBI-3504

PARTS LIST

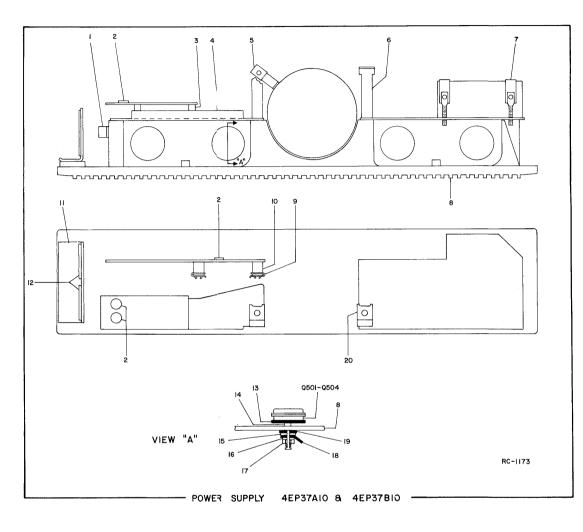
LBI-3582J

C1	SYMBOL	GE PART NO.	DESCRIPTION
C1 7774750P1 Ceramic disc: .00047 µf +100 -0%, 500 VDCW. C2 5496267P14 Tantalum: 15 µf ±20%, 20 VDCW. C3 19A115680P10 Electrolytic: 200 µf +150% -10%, 18 VDCW; sim to Mallory Type TT. C4 19A116080P107 Polyester: 0.1 µf ±10%, 50 VDCW.	A501*		
C2 5496267P14 C3 19A115680P10 C4 19A116080P107 C4 19A116080P107 C4 19A116080P107 C6 19A116080P107 C7 19A116080P107 C8 1 4037822P1 C8 1 4034664P1 C8 1 4037822P1 C8 1 19A115123P1 C8 1 19A115123P1 C8 1 19A115123P1 C8 1 19A115123P1 C8 1 19A11568P1 C8 1 19A11568P1 C8 1 19A11568P1 C9 1 19A115123P1 C9 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1			
C3 19A115680P10 Electrolytic: 200 µf +150% -10%, 18 VDCW; sim to Mallory Type TT. C4 19A116080P107 Polyester: 0.1 µf ±10%, 50 VDCW. DIGDES AND RECTIFIERS Silicon. CR1 4037822P1 Silicon. DS1* 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. Deleted by REV S. TRANSISTORS Q1 19A115123P1 Silicon, NPN; sim to Type 2N2712. Silicon, NPN; sim to Type 2N2712. Silicon, PNP; sim to Type 2N3702. RESISTORS R1 3R77P680K Composition: 68 chms ±10%, 1/2 w. Composition: 100 chms ±5%, 1/2 w. Composition: 100 chms ±5%, 1/2 w. Composition: 0.10 megchm ±10%, 1/2 w. Composition: 0.10 megchm ±10%, 1/2 w. In REV M and earlier: 3R77P103K Composition: 10,000 chms ±10%, 1/2 w. Composition: 10,000 chms ±10%, 1/2 w. Composition: 220 chms ±5%, 1/2 w. Added by REV S VOLTAGE REGULATORS VR1 4036887P6 Silicon, Zener. IN REV H thru L: 10 VOLT REGULATOR BOARD 19C303420G7 -	Ċ1	7774750Pl	Ceramic disc: .00047 µf +100 -0%, 500 VDCW.
to Mallory Type TT. Polyester: 0.1 \(\mu f \) tlO%, 50 VDCW. DIODES AND RECTIFIERS Silicon. DS1* 4034664Pl	C2	5496267P14	Tantalum: 15 μf ±20%, 20 VDCW.
CRI 4037822P1 Silicon.	C3	19A115680P10	Electrolytic: 200 µf +150% -10%, 18 VDCW; sim to Mallory Type TT.
Silicon.	C4	19Al16080Pl07	Polyester: 0.1 µf ±10%, 50 VDCW.
DS1* 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. Deleted by REV S. 194115123P1 Silicon, NPN; sim to Type 2N2712. Silicon, NPN; sim to Type 2N2712. Silicon, NPN; sim to Type 2N3702.			DIODES AND RECTIFIERS
DS1* 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. Deleted by REV S.	CR1	4037822P1	Silicon.
DS1* 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. Deleted by REV S.			INDICATING DEVICES
Q1	ns1 *	4034664P1	
Q1	™1.	1001001F1	by REV S.
R1 3R77P680K Composition: 68 ohms ±10%, 1/2 w.			TRANSISTORS
R1 3R77P680K Composition: 68 ohms ±10%, 1/2 w. R2 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R3 3R77P101J Composition: 100 ohms ±5%, 1/2 w. R4 19A115681P1 Variable, wirewound: 1000 ohms ±20%, 3 w; sim to CTS Series 115. R5 3R77P104K Composition: 0.10 megohm ±10%, 1/2 w. Composition: 1000 ohms ±10%, 1/2 w. In REV M and earlier: 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. In REV M and earlier: Composition: 220 ohms ±5%, 1/2 w. Added by REV S	Q1	19All5123Pl	Silicon, NPN; sim to Type 2N2712.
R1 3R77P680K Composition: 68 ohms ±10%, 1/2 w. R2 3R77P33LJ Composition: 330 ohms ±5%, 1/2 w. R3 3R77P10LJ Composition: 100 ohms ±5%, 1/2 w. R4 19A115681P1 Variable, wirewound: 1000 ohms ±20%, 3 w; sim to CTS Series 115. R5 3R77P104K Composition: 0.10 megohm ±10%, 1/2 w. R6* 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. In REV M and earlier: 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. Composition: 220 ohms ±5%, 1/2 w. Added by REV S VOLTAGE REGULATORS Silicon, Zener. R501* L10 VOLT REGULATOR BOARD 19C303420G7 CAPACITORS CAPACITORS	Q2	19A115768P1	Silicon, PNP; sim to Type 2N3702.
R2 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R3 3R77P101J Composition: 100 ohms ±5%, 1/2 w. R4 19A115681P1 Variable, wirewound: 1000 ohms ±20%, 3 w; sim to CTS Series 115. R5 3R77P104K Composition: 0.10 megohm ±10%, 1/2 w. R6* 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. In REV M and earlier: 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. In REV M and earlier: 3R77P221J Composition: 220 ohms ±5%, 1/2 w. Added by REV S VOLTAGE REGULATORS VR1 4036887P6 Silicon, Zener. LIN REV H thru L: 10 VOLT REGULATOR BOARD 19C303420G7 CAPACITORS CAPACITORS CAPACITORS CAPACITORS CAPACITORS CAPACITORS CAPACITORS CAPACITORS CAPACITORS Silicon, Zener. C4 7774750P1 Ceramic disc: .00047 µf +100 -0%, 500 VDCW. C5 5496267P14 Tantalum: 15 µf ±20%, 20 VDCW. C6 19A115680P10 Electrolytic: 200 µf +150% -10%, 18 VDCW; sim to Mallory Type TT			
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to CTS Series 115. Composition: 0.10 megohm ±10%, 1/2 w. R6* 3R77P102K	R3	3R77P101J	Composition: 100 ohms ±5%, 1/2 w.
R5 3R77P104K Composition: 0.10 megohm ±10%, 1/2 w. R6* 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. In REV M and earlier: Composition: 10,000 ohms ±10%, 1/2 w. R7* 3R77P221J Composition: 220 ohms ±5%, 1/2 w. Added by REV S	R4	19Al15681P1	Variable, wirewound: 1000 ohms ±20%, 3 w; sim to CTS Series 115.
In REV M and earlier: Composition: 10,000 ohms ±10%, 1/2 w. Composition: 220 ohms ±5%, 1/2 w. Added by REV S	R5	3R77P104K	
3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. 3R77P22lJ Composition: 220 ohms ±5%, 1/2 w. Added by REV S	R6*	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.
R7* 3R77P221J Composition: 220 ohms ±5%, 1/2 w. Added by REV S			In REV M and earlier:
VR1 4036887P6 Silicon, Zener. IN REV H thru L: 10 VOLT REGULATOR BOARD 19C303420G7		3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
VR1	R7*	3R77P221J	Composition: 220 ohms ±5%, 1/2 w. Added by REV S
IN REV H thru L: 10 VOLT REGULATOR BOARD 19C303420G7			VOLTAGE REGULATORS
A501* 10 VOLT REGULATOR BOARD 19C303420G7	VR1	4036887P6	Silicon, Zener.
19C303420G7			IN REV H thru L:
C4 7774750P1 Ceramic disc: .00047 µf +100 -0%, 500 VDCW. C5 5496267P14 Tantalum: 15 µf ±20%, 20 VDCW. C6 19A115680P10 Electrolytic: 200 µf +150% -10%, 18 VDCW; sim to Mallory Type TT. CR3 4037822P1 Silicon. DS1 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. Q5 19A115123P1 Silicon, NPN; sim to Type 2N2712.	A501*		10000040000
C4 7774750P1 Ceramic disc: .00047 µf +100 -0%, 500 VDCW. C5 5496267P14 Tantalum: 15 µf ±20%, 20 VDCW. C6 19A115680P10 Electrolytic: 200 µf +150% -10%, 18 VDCW; sim to Mallory Type TT. DIODES AND RECTIFIERS CR3 4037822P1 Silicon. DS1 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. Q5 19A115123P1 Silicon, NPN; sim to Type 2N2712.		İ	19C3U342UG/ _
C5 5496267P14 Tantalum: 15 µf ±20%, 20 VDCW. C6 19A115680P10 Electrolytic: 200 µf +150% -10%, 18 VDCW; sim to Mallory Type TT. DIODES AND RECTIFIERS CR3 4037822P1 Silicon. DS1 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. TRANSISTORS Q5 19A115123P1 Silicon, NPN; sim to Type 2N2712. RESISTORS			
C6 19A115680P10 Electrolytic: 200 µf +150% -10%, 18 VDCW; sim to Mallory Type TT. DIODES AND RECTIFIERS Silicon. DS1 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. TRANSISTORS Q5 19A115123P1 Silicon, NPN; sim to Type 2N2712. RESISTORS		i	
to Mallory Type TT. DIODES AND RECTIFIERS Silicon. INDICATING DEVICES Lamp, incandescent: 28 v; sim to GE2148. TRANSISTORS Q5 19A115123P1 Silicon, NPN; sim to Type 2N2712. RESISTORS			
CR3 4037822P1 Silicon. INDICATING DEVICES Lamp, incandescent: 28 v; sim to GE2148. TRANSISTORS Q5 19A115123P1 Silicon, NPN; sim to Type 2N2712. RESISTORS			
DS1 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. Q5 19A115123P1 Silicon, NPN; sim to Type 2N2712.			DIODES AND RECTIFIERS
DS1 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. TRANSISTORS Silicon, NPN; sim to Type 2N2712. RESISTORS	CR3	4037822P1	Silicon.
Q5			INDICATING DEVICES
Q5	DS1	4034664P1	Lamp, incandescent: 28 v; sim to GE2148.
Q5			
RESISTORS	Q5	19A115123P1	
	•		
R8 $3R77P680K$ Composition: 68 ohms $\pm 10\%$, $1/2$ w.		3R77P680K	

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
R9	3R77P331J	Composition: 330 ohms ±5%, 1/2 w.			VOLTAGE REGULATORS
R10	3R77P101J	Composition: 100 ohms ±5%, 1/2 w.	VR1	4036887P9	Silicon, Zener.
RII	19A115681P1	Variable, wirewound: 1000 ohms ±20%, 3 w; sim			Í
1122	20112000212	to CTS Series 115.			
		VOLTAGE REGULATORS	C501 thru	19B209004P11	Polyester: 0.68 μf ±10%, 100 VDCW; sim to Sprague 157P68491.
VR4	4036887P6	Silicon, Zener.	C504 C505	5403.656P40	7-1
		TV DVV D 4b C	and C506	5491656P42	Polyester: 0.47 µf ±20%, 400 VDCW; sim to GE Type 61F.
501*		IN REV D thru G: 10 VOLT REGULATOR BOARD	C507	5491656P40	Polyester: 1 µf +30% -10%, 1000 VDCW; sim to
301+		19C303420G6			GE Type 61F.
			C509	19C301693P20	Ceramic disc: .006 µf ±10%, 1000 VDCW; sim t RMC Type JF Discap.
C4	7774750P1	Ceramic disc: .00047 µf +100 -0%, 500 VDCW.	C512*	19A115028P14	Polyester: 0.1 µf ±20%, 200 VDCW. Added by
C5	5496267P14	Tantalum: 15 μf ±20%, 20 VDCW; sim to			REV B.
		Sprague Type 150D.	C513* and	19A11680P10	Electrolytic: 200 µf +150% -10%, 18 VDCW; si to Mallory Type TT. Added by REV P.
		DIODES AND RECTIFIERS	C514*		DIODEG AND SECURITIONS
CR2*	19A115250Pl	Silicon. Deleted by REV J.	CR501	4027899p1	DIODES AND RECTIFIERS
CR3*	4037822P1	Silicon. Added by REV J.	thru CR506	4037822P1	Silicon.
		INDICATING DEVICES	CR506	19A115845P4	Silicon,
201	100100171		thru CR510	10/11001011	officer.
DS1	4034664P1	Lamp, incandescent: 28 v; sim to GE 1762D.	I Children		INDUCTORS
		TRANSISTORS	L501	19A121120P1	Reactor: 0.45 h +0.505 h min at 0.15 amp DC, 20 ohms ±10% DC res, 1000 v peak, 420 VDC
Q5	19A115123P1	Silicon, NPN; sim to Type 2N2712.			operating.
		RESISTORS	L502	19B200777P1	Reactor: 0.1 h min at 0.15 amp DC, 12 ohms ±10% DC res, 720 v peak, 300 VDC operating.
R8*	3R77P680K	Composition: 68 ohms ±10%, 1/2 w.	L503	19A115391P1	Coil, RF: 50 µh ±10% ind at 1000 Hz, .02 ohr
		In REV D:			DC res max.
	3R77P161J	Composition: 160 ohms ±5%, 1/2 w.			TRANSISTORS
R9	3R77P331J	Composition: 330 ohms ±5%, 1/2 w.	Q501	5490810P1	Germanium, PNP.
R10	3R77Pl01J	Composition: 100 ohms ±5%, 1/2 w.	thru Q504		
R11	19A115681P1	Variable, wirewound: 1000 ohms ±20%, 2.2 w; sim to CTS Series 115.	Q506	19A115341P1	Germanium, PNP.
		Sim to Cib Beries 113.	Q507	19A115768P1	Silicon, PNP; sim to Type 2N3702.
		VOLTAGE REGULATORS			
VR4	4036887P6	Silicon, Zener.	R501	5493035P3	Wirewound, ceramic: 2 ohms ±5%, 5 w; sim to
		IN REV C AND EARLIER	and R502		Hamilton Hall Type HR.
A501*		REGULATOR COMPONENT BOARD ASSEMBLY	R503	5493035P4	Wirewound, ceramic: 80 ohms ±5%, 5 w; sim to
		19C303420G1	and R504		Hamilton Hall Type HR.
		CAPACITORS	R505	3R77P222K	Composition: 2200 ohms ±10%, 1/2 w.
Cl	5496267P10	Tantlaum: 22 μf ±20%, 15 VDCW; sim to Sprague	R506	3R77P751J	Composition: 750 ohms ±5%, 1/2 w.
		Type 150D.	R507	3R77P822K	Composition: 8200 ohms $\pm 10\%$, $1/2$ w.
		DIODES AND RECTIFIERS	R508	19B209113P3	Variable, wirewound: 1000 ohms ±20%, 2.5 w.
CR1	4037822P1	Silicon.	R509	3R77P222K	Composition: 2200 ohms $\pm 10\%$, $1/2$ w.
			R510 and	3R77P394K	Composition: 0.39 megohm ±10%, 1/2 w.
Q1 *	4037993P1	Germanium, PNP; sim to Type 2N1303. Deleted	R511		
		by REV C.	R512	3R77P751J	Composition: 750 ohms ±5%, 1/2 w.
Q2	19C300073P2	Germanium, PNP; sim to Type 2N1414.	R513	5493035P4	Wirewound, ceramic: 80 ohms $\pm 5\%$, 5 w; sim to Hamilton Hall Type HR.
Q3	19A115123P1	Silicon, NPN; sim to Type 2N2712.			
			-503.		
Rl	3R77P680J	Composition: 68 ohms $\pm 5\%$, $1/2$ w.	T501*	19C304106G3	Transformer. In REV E and earlier:
R3	3R77P242J	Composition: 2400 ohms ±5%, 1/2 w.		19C304106G1	In REV E and earlier: Transformer.
R4	3R77P331J	Composition: 330 ohms ±5%, 1/2 w.		13030410061	TI WIND T OF HIGH
R5	3R77P681J	Composition: 680 ohms ±5%, 1/2 w.			TERMINAL BOARDS
R6	19B209113P1	Variable, wirewound: 250 ohms ±20%, 2.5 w.	TBl	19C303431G1	Eyelet board.
R8*	3R77P680K	Composition: 68 ohms $\pm 10\%$, $1/2$ w. Added by REV C.	TB2	19B204509G1	Eyelet board.
					1

SYMBOL	GE PART NO.	DESCRIPTION
твз	19B204463G1	Eyelet board.
TB4	19B204463G2	Eyelet board.
тв5	19C303422G1	Eyelet board.
VR501	4036887P6	Silicon, Zener.
		HARNESS ASSEMBLY 19D402277G3
C511	19A115028P17	Polyester: 0.33 µf ±20%, 100 VDCW.
		JACKS AND RECEPTACLES
J504	19A121524G1	Connector, phen: 8 contacts.
P501 and P502	19B209151P1	Terminal: solderless; sim to Amp 42284-5.
P505	19B204781P1	Female, phen: No. 1 thru 12 contacts rated at 2 amps at 850 VDC max, No. 13 contact rated at 4 amps at 450 VDC max.
05054		TRANSISTORS
Q505*	19A116203P3	Silicon, NPN.
		In REV K:
	19A116118P1	Silicon, NPN.
		In REV G, H and J:
	19A115948P1	Silicon, NPN.
		In REV D, E and F:
	19A115527P1	Germanium, PNP.
	19A115267P1	In REV C and earlier: Germanium, PNP.
XQ506	5491888P1	Transistor, power, phen: sim to Cinch 133-92-10-034.
		MISCELLANEOUS
	19C303390P2	Power Supply cover.
		MECHANICAL PARTS (SEE RC-1173)
1	7763541P4	Cable clamp. (Used with P505 cable).
2	4036555P1	Insulator, washer: nylon. (Used with Q1, Q2).
3	7140624P6	Spacer. (Used with A501).
4	19C303429P1	Support. (Used with A501).
5	7160861P2	Speed nut: spring; sim to Tinnerman C880-632-157. (Used with T501).
6	19A121220P1	(Not Used).
7	19B204454Gl	(Not Used).
8	19D402261P1	Heat sink.
9	7160861P10	(Not Used).
10	7142162P89	(Not Used).
11	19B204431P1	Support. (Used with Q505 and Q506).
12	4029974P1	Transistor insulator. (Used with Q505 and Q506)
13	4031291P1	Transistor insulator. (Used with Q501 and Q502)
14	4034215P1	Bushing. (Used with Q501 and Q502).
15	4024225P1	Flat washer. (Used with Q501 and Q502).
16	N405P9Cl3	Lockwasher. No. 10. (Used with Q501 and Q502).
	4032596P1	Nut. No. 10-32. (Used with Q501 and Q502).
17	1	Solder terminal: sim to Shakeproof 214-14-000.
17 18	4036835P1	(Used with Q501 and Q502).
	4036835P1 19A115221P3	

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES



PRODUCTION CHANGES

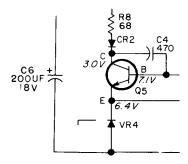
Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A To protect the 10-volt regulator against reverse polarity.

 Added CRl to the 10-volt regulator board A501.
- REV. B To suppress switching spikes in the power supply primary. Added C512.
- REV. C To improve operation of 10-volt regulator. Deleted Q1 and added R8 to the 10-volt regulator board A501.
- REV. D To improve reliability of 10-volt regulator. Changed Q505 and 10-volt regulator circuit (A501).
- REV. E To improve operation of 10-volt regulator A501. Changed R8.
- REV. F To provide tap for 120-watt input. Changed T501.
- REV. G To incorporate new transistor. Changed Q505.
- REV. H To reduce alternator noise. Changed A501.
- REV. J To provide reverse polarity protection. Deleted CR2 and added CR3 to 10-volt regulator A501

Schematic Diagram

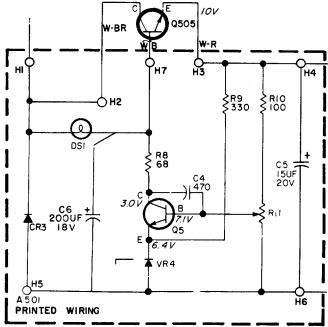
Was



- Rev. K To incorporate a different transistor. Changed Q505.
- Rev. L To obtain a more reliable connection to the regulator transistor. Changed Q505.
- Rev. M To incorporate a transistor switch on the 10-volt regulator board for receiver muting. Added C4, R5, R6, Q2 and new regulator board.

Schematic Diagram

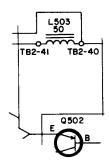
Was:



10-VOLT REGULATOR

- REV. N To insure muting of the receiver when operating below 20% of the battery voltage. Changed R6.
- REV. P To reduce residual spike deviation. Added C513 and C514.

Schematic Diagram was



- REV. R To improve performance and mechanical construction. Added standoffs. Changed cover and DA wire between TB5-32 and TB2-40.
- REV. S To solve procurement problem.

 10 Volt Regulator Board, 19C317751G1
 Deleted DS1 and added R7.
 10 Volt Regulator Board, 19C303420G6
 Deleted DS1 and added R12.
- REV. T To improve filtering. Changed connection of C513 and C514.